

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S85	2	"20040005731".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/20 17:19
S72	50	(chamber or reactor) and (cvd or chemical near2 vapor near2 deposit\$4) and (heat\$5 near5 surround\$6) near10 walls and rotat\$4 near5 (substrate wafer or susceptor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/21 14:35
S8	23	(johannes near2 kaeppler or frank near2 wischmeyer or gert near2 strauch).in. and cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/21 14:35
L2	28	(johannes near2 kaeppler or frank near2 wischmeyer or gert near2 strauch).in. and cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/21 14:35
L1	50	(chamber or reactor) and (cvd or chemical near2 vapor near2 deposit\$4) and (heat\$5 near5 surround\$6) near10 walls and rotat\$4 near5 (substrate wafer or susceptor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/21 14:35
S26	12	horizontal near6 (flow or reactor) and (sic or silicon near2 carbide near4 germanium) near5 (cvd or chemical near2 vapor near2 deposit\$6) and @py<"2002" and (substrate or susceptor) near10 temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/21 14:36
S23	72	horizontal near6 (flow or reactor) and (sic or silicon near2 carbide) near5 (cvd or chemical near2 vapor near2 deposit\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/21 14:36
S11	70	activ\$5 near4 flow near2 channel and (cvd or chemical near2 vapor near2 deposit\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/21 14:36
L5	12	horizontal near6 (flow or reactor) and (sic or silicon near2 carbide near4 germanium) near5 (cvd or chemical near2 vapor near2 deposit\$6) and @py<"2002" and (substrate or susceptor) near10 temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/21 14:36

## EAST Search History

L4	76	activ\$5 near4 flow near2 channel and (cvd or chemical near2 vapor near2 deposit\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/21 14:36
L6	84	horizontal near6 (flow or reactor) and (sic or silicon near2 carbide) near5 (cvd or chemical near2 vapor near2 deposit\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/21 14:37
L3	1	(johannes near2 kaeppler or frank near2 wischmeyer or gert near2 strauch).in. and chemical near2 vapor near2 deposit\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/21 14:37
S77	127	rotat\$5 near5 (wafer or susceptor or substrate) and (heat\$4 or hot) near2 wall same (cvd or chemical near2 vapor near2 deposit\$4) and @py<"2003"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/21 14:38
S38	93	inlet near5 cool\$6 near10 react\$5 and cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/21 14:38
L8	127	rotat\$5 near5 (wafer or susceptor or substrate) and (heat\$4 or hot) near2 wall same (cvd or chemical near2 vapor near2 deposit\$4) and @py<"2003"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/21 14:38
L7	98	inlet near5 cool\$6 near10 react\$5 and cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/21 14:38